

MAMF-011183

Rev. V1

#### **Features**

- Broadband Performance, 20 to 44 GHz
- Low Loss <1.0 dB
- High Isolation >34 dB
- Up to 13 W CW Power, +85°C
- 23 dBm Power Handling in Terminated Port
- TTL Compatible Driver
- -10 V to -25 V Back Bias
- Quiescent Currents <1 mA
- Lead-Free 5 x 4 mm PQFN package
- RoHS\* Compliant

## **Applications**

- 5G
- Point-to-Point
- Radar
- Radiometers
- **Test & Instrumentation**
- High Frequency Applications

## **Description**

The MAMF-011183 is a high power SPDT PIN diode switch with integrated driver in 5 x 4 mm PQFN package. This broadband, high linearity, SPDT switch with 50  $\Omega$  terminated RF ports was developed for Ka-Band applications that require up to 13 W power handling at an environmental temperature of +85°C while maintaining low insertion loss and high isolation.

The SPDT MMIC utilizes MACOM's proven AlGaAs PIN diode technology.

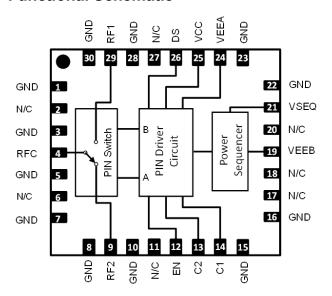
The included driver utilize MACOM developed PIN diode driver MADR-011022 and characteristic of this driver.

## Ordering Information<sup>1</sup>

Part Number	Package
MAMF-011183-TR0500	500 piece reel
MAMF-011183-SMB	Sample Board

1. All sample boards include 5 loose parts.

#### **Functional Schematic**



## Pin Configuration<sup>2</sup>

Pin #	Function	Description
1, 3, 5, 7, 8,10,15, 16, 22, 23,28, 30	GND	Ground
2, 6, 11, 17, 18, 20, 27	N/C	No Connection
4	RFC	RF Common Port
9	RF2	Terminated RF Port 2
12	EN	Enable
13	C2	Logic Control Input
14	C1	Logic Control Input
19	VEEB	Negative Sequencer Bias
21	VSEQ	Power Sequencer Output
24	VEEA	Negative Driver Bias
25	VCC	Positive Bias
26	DS	Driver Select
29	RF1	Terminated RF Port 1
31	Paddle <sup>3</sup>	RF, DC & Thermal Ground

- 2. MACOM recommends connecting unused package pins to
- ground.
  3. The exposed pad centered on the package bottom must be

<sup>\*</sup> Restrictions on Hazardous Substances, compliant to current RoHS EU directive.



MAMF-011183

Rev. V1

## **Electrical Specifications:**

Freq. = 20 - 44 GHz,  $T_A$  = 25°C,  $V_{CC}$  = +4.5 V @ 29 mA / -20 V @ 0 mA,  $Z_0$  = 50  $\Omega$ 

Parameter   Test Conditions   Units   Min.   Typ.   Max.						
Insertion Loss	Parameter	Test Conditions	Units	Min.	Тур.	Max.
Isolation   Solation   Solatio	Insertion Loss	28 GHz 35 GHz	dB	_	0.9 1.0	
Input / Output Return Loss On state	Isolation <sup>4</sup>	28 GHz 35 GHz	dB	32 32 —	40 38	_
RF1, 2 Return Loss, Off state       28 GHz 35 GHz 41 GHz 213       dB       —       9 5 13       —         Switching Speed-T <sub>OFF</sub> 50% DC to 90% RF       ns       —       36       —         Switching Speed-T <sub>OFF</sub> 50% DC to 10% RF       ns       —       33       —         Rise Time -T <sub>RISE</sub> 10% to 90% RF       ns       —       4       —         Fall Time - T <sub>FALL</sub> 90% to 10% RF       ns       —       13       —         CW Input Power <sup>5</sup> -25 V @ +85°C       dBm       —       41.2       —         V <sub>CC</sub> Quiescent Current (I <sub>CC</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         V <sub>EEB</sub> Quiescent Current (I <sub>EEB</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup> Control = 5 V       μA       —       20       25         R <sub>PULL-UP</sub> , Output Pull-up On Resistance       43 mA Load       Ω       —       19       25         R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequ		28 GHz 35 GHz	dB	_	19 19	_
Switching Speed-T <sub>OFF</sub> 50% DC to 10% RF         ns         —         33         —           Rise Time -T <sub>RISE</sub> 10% to 90% RF         ns         —         4         —           Fall Time - T <sub>FALL</sub> 90% to 10% RF         ns         —         13         —           CW Input Power <sup>5</sup> -25 V @ +85°C         dBm         —         41.2         —           V <sub>CC</sub> Quiescent Current (I <sub>CC</sub> )         C1 = 5 V, C2 = DS = EN = 0 V         mA         —         0.4         0.5           V <sub>EEB</sub> Quiescent Current (I <sub>CEB</sub> )         C1 = 5 V, C2 = DS = EN = 0 V         mA         —         0.4         0.5           Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup> Control = 5 V         μA         —         20         25           R <sub>PULL-UP</sub> , Output Pull-up On Resistance         43 mA Load         Ω         —         19         25           R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance         43 mA Load         Ω         —         19         25           Power Sequencer Threshold Voltage         Note 7         V         —         2.5         —           Power Die Power Up Time         Note 8         μs         —         1         —	RF1, 2 Return Loss, Off state	28 GHz 35 GHz	dB	_	9 25	_
Rise Time -T <sub>RISE</sub> 10% to 90% RF       ns       —       4       —         Fall Time - T <sub>FALL</sub> 90% to 10% RF       ns       —       13       —         CW Input Power <sup>5</sup> -25 V @ +85°C       dBm       —       41.2       —         V <sub>CC</sub> Quiescent Current (I <sub>CC</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         V <sub>EEB</sub> Quiescent Current (I <sub>CEB</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup> Control = 5 V       μA       —       20       25         R <sub>PULL-UP</sub> , Output Pull-up On Resistance       43 mA Load       Ω       —       19       25         R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8       μs       —       25       —         Driver Die Power Up Time       Note 9       μs       —       1       —	Switching Speed-T <sub>ON</sub>	50% DC to 90% RF	ns	_	36	_
Fall Time - T <sub>FALL</sub> 90% to 10% RF       ns       —       13       —         CW Input Power <sup>5</sup> -25 V @ +85°C       dBm       —       41.2       —         V <sub>CC</sub> Quiescent Current (I <sub>CC</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         V <sub>EEB</sub> Quiescent Current (I <sub>CEB</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup> Control = 5 V       μA       —       20       25         R <sub>PULL-UP</sub> , Output Pull-up On Resistance       43 mA Load       Ω       —       19       25         R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8       μs       —       1       —         Driver Die Power Up Time       Note 9       μs       —       1       —	Switching Speed-T <sub>OFF</sub>	50% DC to 10% RF	ns	_	33	_
CW Input Power5 $-25 \text{ V } @ +85^{\circ}\text{C}$ dBm $ 41.2$ $ V_{CC}$ Quiescent Current ( $I_{CC}$ ) $C1 = 5 \text{ V}$ , $C2 = DS = EN = 0 \text{ V}$ mA $ 0.4$ $0.5$ $V_{EEB}$ Quiescent Current ( $I_{EEB}$ ) $C1 = 5 \text{ V}$ , $C2 = DS = EN = 0 \text{ V}$ mA $ 0.4$ $0.5$ Control Input Leakage Current ( $I_{CTL}$ )6 $Control = 5 \text{ V}$ $\mu$ A $ 20$ $25$ $R_{PULL-UP}$ , Output Pull-up On Resistance $43 \text{ mA Load}$ $\Omega$ $ 19$ $25$ $R_{PULL-DOWN}$ , Output Pull-down On Resistance $43 \text{ mA Load}$ $\Omega$ $ 19$ $25$ $Power Sequencer Threshold Voltage$ $Note 7$ $V$ $ 2.5$ $ Power Sequencer Power On Time$ $Note 8$ $\mu$ s $ 25$ $ Power Die Power Up Time$ $Power Up Time$	Rise Time -T <sub>RISE</sub>	10% to 90% RF	ns	_	4	_
$V_{CC}$ Quiescent Current ( $I_{CC}$ ) $C1 = 5 \text{ V}$ , $C2 = DS = EN = 0 \text{ V}$ $N_{EEB}$ Quiescent Current ( $I_{EEB}$ ) $C1 = 5 \text{ V}$ , $C2 = DS = EN = 0 \text{ V}$ $N_{CO}$	Fall Time - T <sub>FALL</sub>	90% to 10% RF	ns	_	13	_
V <sub>EEB</sub> Quiescent Current (I <sub>EEB</sub> )       C1 = 5 V, C2 = DS = EN = 0 V       mA       —       0.4       0.5         Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup> Control = 5 V $\mu$ A       —       20       25         R <sub>PULL-UP</sub> , Output Pull-up On Resistance       43 mA Load       Ω       —       19       25         R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8 $\mu$ s       —       25       —         Driver Die Power Up Time       Note 9 $\mu$ s       —       1       —	CW Input Power <sup>5</sup>	-25 V @ +85°C	dBm	_	41.2	_
Control Input Leakage Current ( $I_{CTL}$ ) <sup>6</sup> Control = 5 V $\mu$ A — 20 25 $R_{PULL-UP}$ , Output Pull-up On Resistance 43 mA Load $\Omega$ — 19 25 $R_{PULL-DOWN}$ , Output Pull-down On Resistance 43 mA Load $\Omega$ — 19 25  Power Sequencer Threshold Voltage Note 7 V — 2.5 — Power Sequencer Power On Time Note 8 $\mu$ S — 25 — Driver Die Power Up Time Note 9 $\mu$ S — 1 —	V <sub>CC</sub> Quiescent Current (I <sub>CC</sub> )	C1 = 5 V, C2 = DS = EN = 0 V	mA	_	0.4	0.5
RPULL-UP, Output Pull-up On Resistance       43 mA Load       Ω       —       19       25         RPULL-DOWN, Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8       μs       —       25       —         Driver Die Power Up Time       Note 9       μs       —       1       —	V <sub>EEB</sub> Quiescent Current (I <sub>EEB</sub> )	C1 = 5 V, C2 = DS = EN = 0 V	mA	_	0.4	0.5
RPULL-DOWN, Output Pull-down On Resistance       43 mA Load       Ω       —       19       25         Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8       μs       —       25       —         Driver Die Power Up Time       Note 9       μs       —       1       —	Control Input Leakage Current (I <sub>CTL</sub> ) <sup>6</sup>	Control = 5 V	μA	_	20	25
Power Sequencer Threshold Voltage       Note 7       V       —       2.5       —         Power Sequencer Power On Time       Note 8       μs       —       25       —         Driver Die Power Up Time       Note 9       μs       —       1       —	R <sub>PULL-UP</sub> , Output Pull-up On Resistance	43 mA Load	Ω	_	19	25
Power Sequencer Power On Time  Note 8  μs  25  Driver Die Power Up Time  Note 9  μs  1  —	R <sub>PULL-DOWN</sub> , Output Pull-down On Resistance	43 mA Load	Ω	_	19	25
Driver Die Power Up Time Note 9 μs — 1 —	Power Sequencer Threshold Voltage	Note 7	V	_	2.5	_
	Power Sequencer Power On Time	Note 8	μs	_	25	_
Driver Die Power Down Time Note 10 µs — 1 —	Driver Die Power Up Time	Note 9	μs	_	1	_
	Driver Die Power Down Time	Note 10	μs	_	1	_

4. Isolation defined with 1 port in low loss state.

6. This leakage current is due to an active pull-down NMOS FET at the control input.

7. When  $V_{CC}$  is below this threshold, the internal power sequencer will pull its output  $V_{SEQ}$  to ground.

9. This is the time needed for the driver to function properly after  $V_{CC}$  and  $V_{EEA}$  reach 90% of their stable value.

10. This is the time needed for the internal bias voltages to discharge to 10% of their steady state value after V<sub>CC</sub> and V<sub>EEA</sub> are powered down.

<sup>5.</sup> Reverse bias voltage V<sub>EEB</sub> should be determined based on working conditions. For example, -25 V @ 41.2 dBm input power. For lower power applications, a less negative voltage can be used. R. Caverly and G. Hiller, "Establishing the Minimum Reverse Bias for a P-I-N Diode in a High Power Switch," IEEE Transactions on Microwave Theory and Techniques, Vol.38, No.12, December 1990. Refer to the power over reverse bias voltage chart on page 5.

<sup>8.</sup> This is the delay between the moment when V<sub>CC</sub> is above the power sequencer threshold to V<sub>SEQ</sub> reaches 90% of steady state value. This is measured with a 47 pF shunt capacitor off pin V<sub>EEA</sub>.



**MAMF-011183** 

Rev. V1

## Recommended Operating Conditions<sup>11</sup>

Parameter	Test Conditions	Units	Min.	Тур.	Max.
V <sub>cc</sub>	_		4.5	5.0	5.5
Icc	RF1=ON, RF2=OFF & RF1=OFF, RF2=ON	mA	29	35	53
Icc	RF1=RF2=OFF	mA	59	70	105
V <sub>EEA</sub> and V <sub>EEB</sub>	_	V	-25	_	-10
C1, C2, EN, DS	Logic "0" Logic "1"	V	0.0 2.0	0.0 V <sub>CC</sub>	0.8 V <sub>CC</sub>
Rise / Fall Time of $V_{\text{CC}}$ And $V_{\text{EEB}}$	_	μs	50	_	_
Temperature	_		-40	+25	+85

<sup>11.</sup> Negative bias should be applied to V<sub>EEB</sub> (pin 6) (see note 5). The sequencer output V<sub>SEQ</sub> should be connected to the driver negative bias V<sub>EEA</sub>. A 47 pF shunt capacitor shall be placed close to pin 11 (V<sub>EEA</sub>).

## Absolute Maximum Ratings 12,13

Parameter	Absolute Maximum		
V <sub>EEA</sub> , V <sub>EEB</sub>	-30 V ≤ V <sub>EEA</sub> ,V <sub>EEB</sub> ≤ +0.5 V		
V <sub>CC</sub>	-0.5 V ≤ V <sub>CC</sub> ≤ +7 V		
C1, C2, EN, DS	-0.5 V ≤ V <sub>CC</sub> ≤ +7 V		
CW Incident Power (Low Loss Port)	41.2 dBm @ +85°C 43.0 dBm @ +25°C		
CW Incident Power (Terminated Port)	23 dBm @ +85°C 26 dBm @ +25°C		
Operating Temperature	-40°C to +85°C		
Storage Temperature	-55°C to +150°C		

<sup>12.</sup> Exceeding any one or combination of these limits may cause permanent damage to this device.

## **Truth Table**

Inputs				Outputs		
EN	DS	C2	C1	RF1	RF2	
1	Х	Х	Х	OFF	OFF	
0	0	0	0	OFF	ON	
0	0	0	1	ON	OFF	
0	1	1	0	OFF	ON	
0	1	1	1	ON	OFF	

## **Handling Procedures**

Please observe the following precautions to avoid damage:

### **Static Sensitivity**

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM class 1A devices.

<sup>13.</sup> MACOM does not recommend sustained operation near these survivability limits.

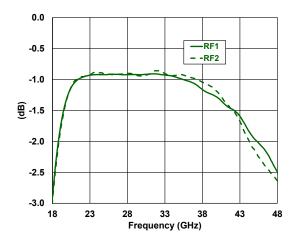


MAMF-011183

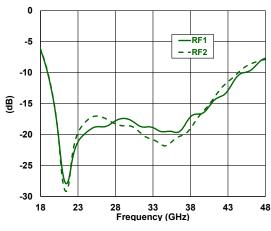
Rev. V1

## Typical Performance Curves @ +25°C

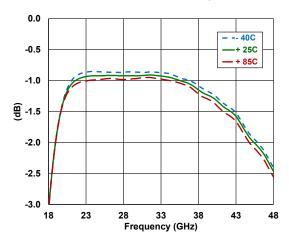
### Insertion Loss (On State)



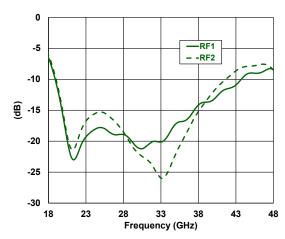
## RF<sub>COMMON</sub> Return Loss (On State)



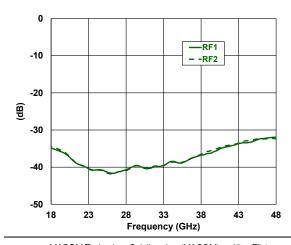
### Insertion Loss (On State) over Temp



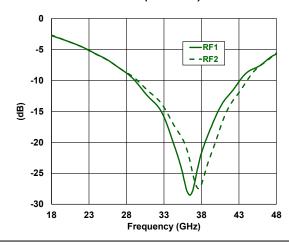
RF1 & RF2 Return Loss (On State)



#### Isolation (Off State)



RF1 & RF2 Return Loss (Off State) Terminated Port



MACOM Technology Solutions Inc. (MACOM) and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

Visit <a href="https://www.macom.com">www.macom.com</a> for additional data sheets and product information.

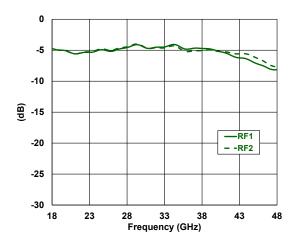


MAMF-011183

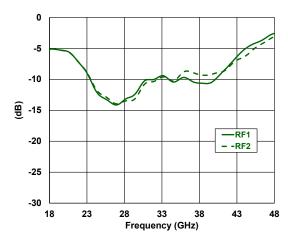
Rev. V1

## Typical Performance Curves @ +25°C

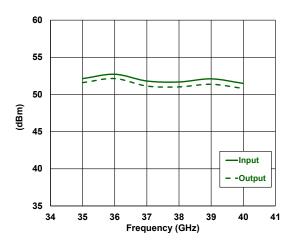
### Insertion Loss (Unbiased)



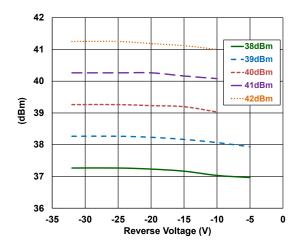
### Return Loss (Unbiased)



### Input Output IP3



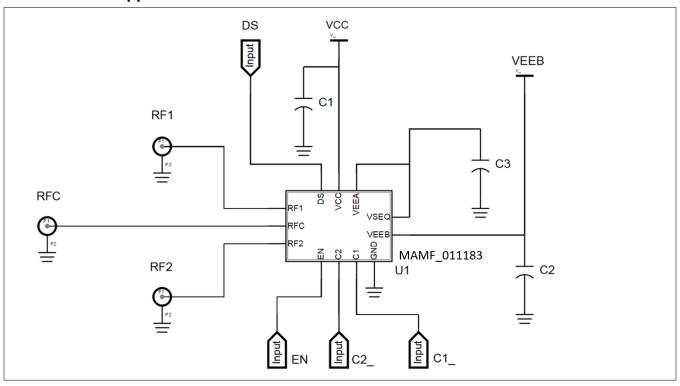
## Output Power over Reverse Bias Voltage @ +85°C, 29 GHz





MAMF-011183 Rev. V1

## MAMF-011183 Application Schematic 14



14. VEEB - recommended -20V, see note 5.

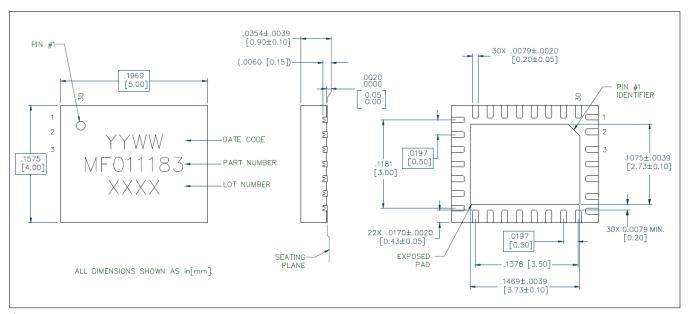
### **Parts List**

Part	Value
C1, C2	0.1 μF
C3	47 pF



MAMF-011183 Rev. V1

### Outline Lead-Free 5 x 4 mm 30-Lead PQFN<sup>†</sup>



<sup>&</sup>lt;sup>†</sup> This is not a JEDEC standard package Reference Application Note M538 for lead-free solder reflow recommendations. Meets JEDEC moisture sensitivity level 1 requirements. Plating is NiPdAuAg



MAMF-011183

Rev. V1

## MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.